URFP064 **Preliminary Power MOSFET**

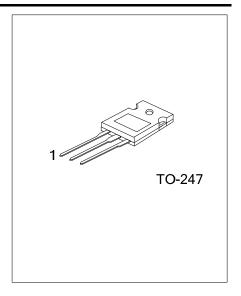
N-CHANNEL 70A, 60V **POWER MOSFET**

DESCRIPTION

The UTC URFP064 is an N-channel enhancement power MOSFET using UTC's advanced technology to provide the customers with a minimum on-state resistance and high switching speed.

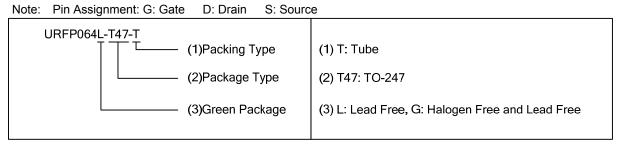
FEATURES

- * $R_{DS(ON)}$ <10m Ω @ V_{GS} =10V, I_D =35A
- * High Switching Speed

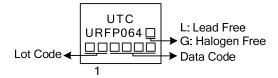


ORDERING INFORMATION

Ordering Number		Deelsess	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
URFP064L-T47-T	URFP064G-T47-T	TO-247	G	D	S	Tube	



MARKING



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ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Drain Current	Continuous	I _D	70	Α	
	Pulsed (Note 2)	I _{DM}	280		
Single Pulsed Avalanche Energy		E _{AS}	1500	mJ	
Power Dissipation		P_{D}	190	W	
Junction Temperature		T_J	-55 ~ + 150	°C	
Storage Temperature		T _{STG}	-55 ~ + 150	°C	

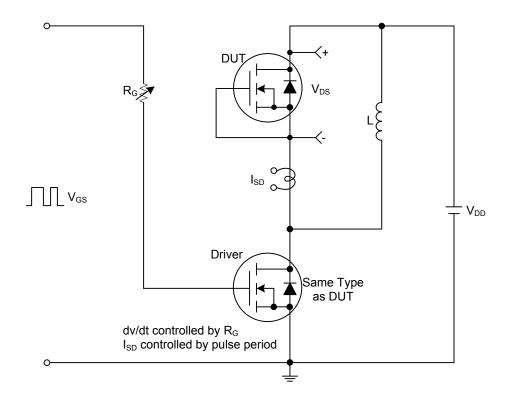
- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 - 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
 - 3. L = 120mH, I_{AS} = 5.0A, V_{DD} = 25V, R_{G} = 25 Ω .

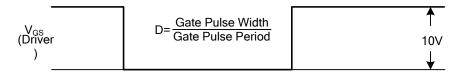
ELECTRICAL CHARACTERISTICS

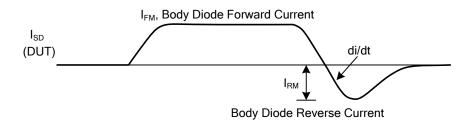
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PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS		1	<u> </u>							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	60			V			
Drain-Source Leakage Current	Drain-Source Leakage Current		V _{DS} =60V, V _{GS} =0V			10	μA			
Gate-Source Leakage Current	Forward	I _{DSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA			
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA			
ON CHARACTERISTICS										
Gate Threshold Voltage		V _{GS(TH)}	I_D =250 μ A, V_{DS} = V_{GS}	2.0		4.0	V			
Static Drain-Source On-State Resistance		R _{DS(ON)}	V_{GS} =10V, I_D =35A			10	mΩ			
DYNAMIC PARAMETERS										
Input Capacitance		C _{ISS})/ O)/)/ O5)/		3800		pF			
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, -f=1.0MHz		960		pF			
Reverse Transfer Capacitance		C _{RSS}	71- 1.0IVIDZ		75		pF			
SWITCHING PARAMETERS										
Total Gate Charge		Q_{G}	1/ 50)/ 1/ 40)/		265		nC			
Gate to Source Charge		Q_{GS}	V _{DD} =50V, V _{GS} =10V,		30		nC			
Gate to Drain Charge		Q_{GD}	-I _D =1.3A, I _G =100μA,		60		nC			
Turn-ON Delay Time		$t_{D(ON)}$			152		ns			
Rise Time		t _R	V_{DD} =30V, I_{D} =0.5A,		304		ns			
Turn-OFF Delay Time Fall-Time		t _{D(OFF)}	$R_G=25\Omega$, $V_{GS}=10V$		600		ns			
		t _F			310		ns			
SOURCE- DRAIN DIODE RATIN	NGS AND CH	ARACTERIS	TICS	•						
Maximum Body-Diode Continuou	us Current	Is				70	Α			
Maximum Body-Diode Pulsed Current		I _{SM}				280	Α			
Drain-Source Diode Forward Voltage		V _{SD}	I _S =70A, V _{GS} =0V			1.28	V			
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =70A, V _{GS} =0V		74					
			dl ₌ /dt=100A/us				ns			
Body Diode Reverse Recovery Charge		Q _{rr}	·		0.2		μC			
Notes: 1. Pulse Test : Pulse widt	h≤300us Du	tv cvcle ≤ 2%		1						
2. Essentially independen	it of operating	temperature.		07						
2. Loodinany maoponaon	it or operating	tomporataro.	TO V	UU,						
			16 10 C							
	42 M 68									
		366	las ilus							
		- Fly	1,117							
		MIN	W.							
	-	4 M								
Body Diode Reverse Recovery Charge Q _{rr} 0.2 Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%. 2. Essentially independent of operating temperature. UNISONIC TECHNOLOGIES CO., LTD www.unisonic.com.tw					2 of 5					
www.unisonic.com.tw					QW-R502-752.b					

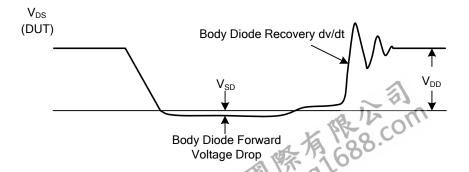


■ TEST CIRCUITS AND WAVEFORMS



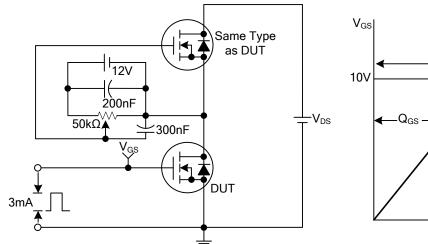






Peak Diode Recovery dv/dt Test Circuit and Waveforms

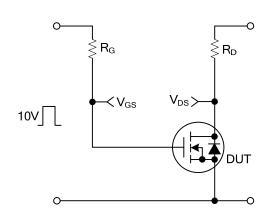
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



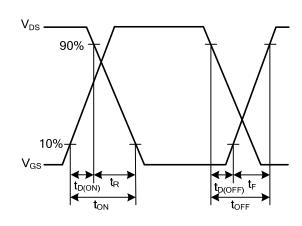
V_{GS}
10V
Q_G
Q_{GD}
Charge

Gate Charge Test Circuit

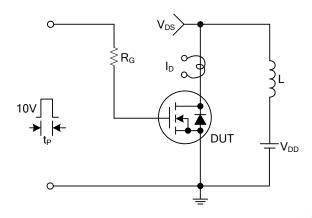
Gate Charge Waveforms



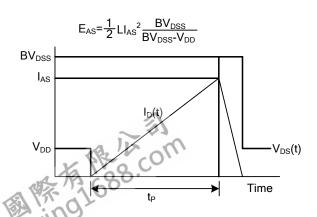
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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